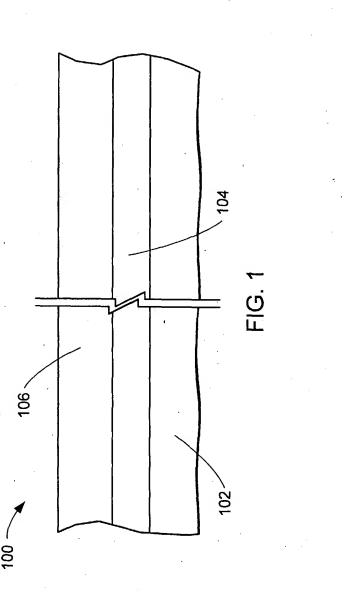
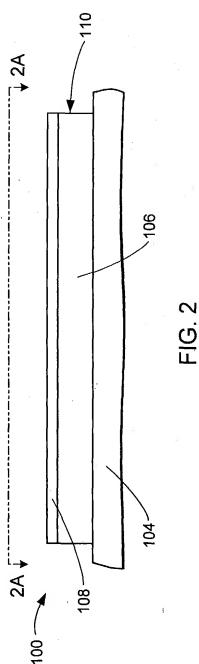
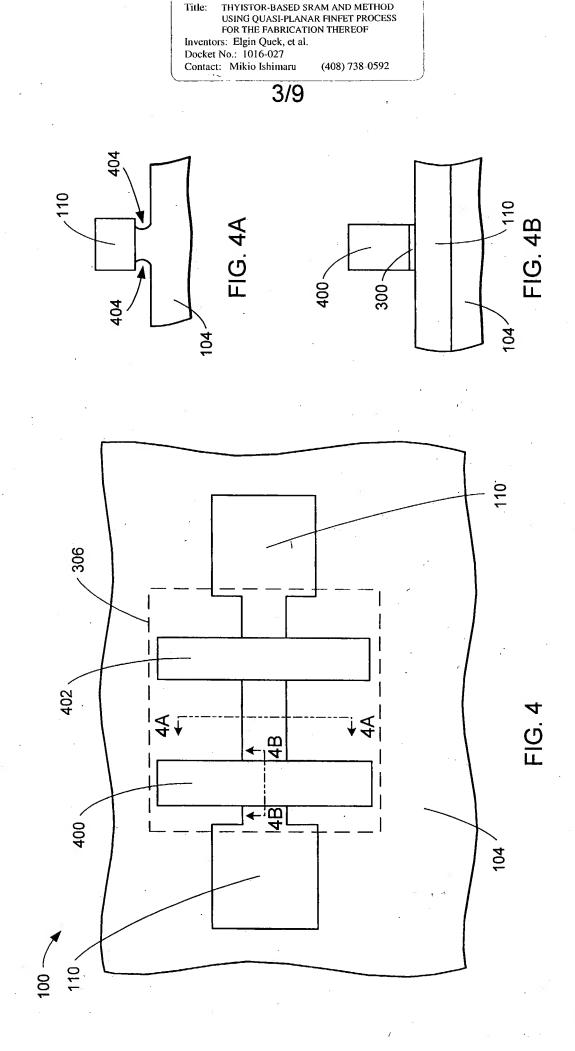
Title: THYISTOR-BASED SRAM AND METHOD USING QUASI-PLANAR FINFET PROCESS FOR THE FABRICATION THEREOF Inventors: Elgin Quek, et al. Docket No.:. 1016-027
Contact: Mikio Ishimaru (408) 738-0592

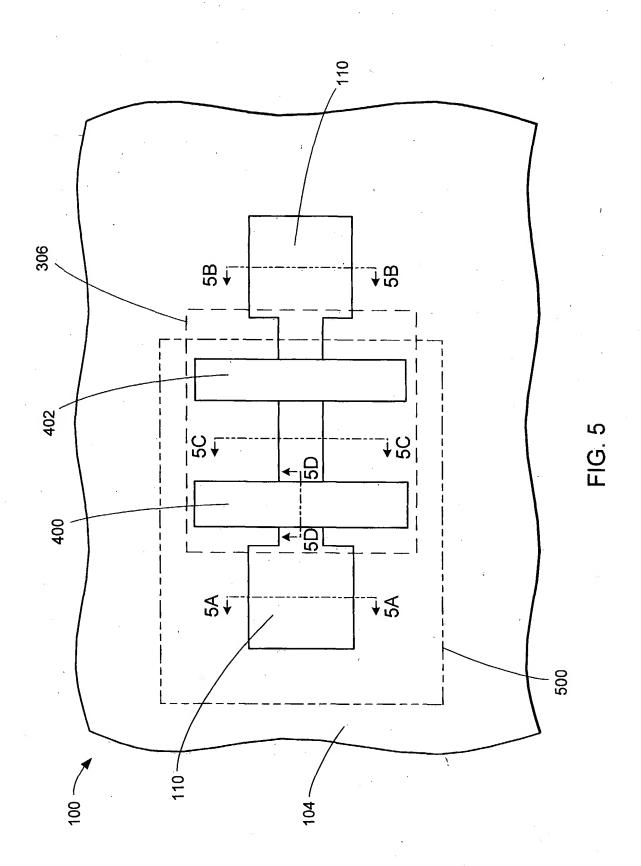




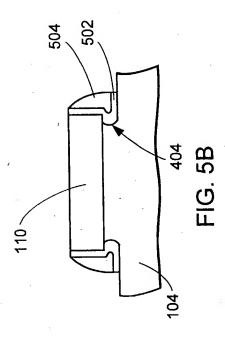
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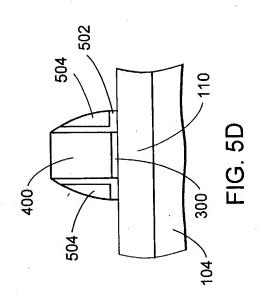


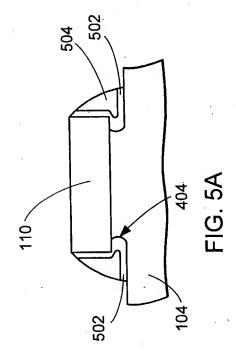
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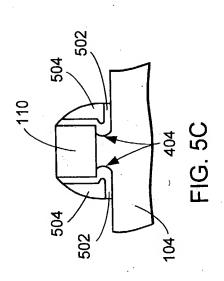


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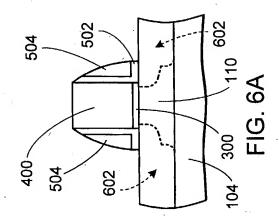


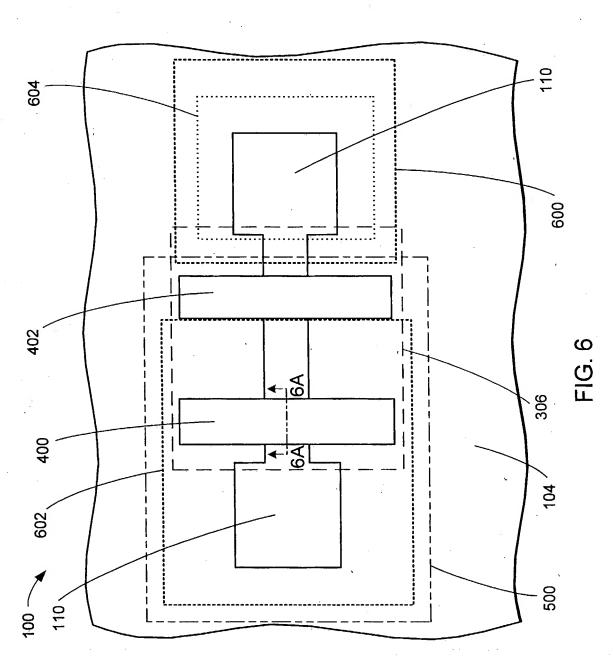






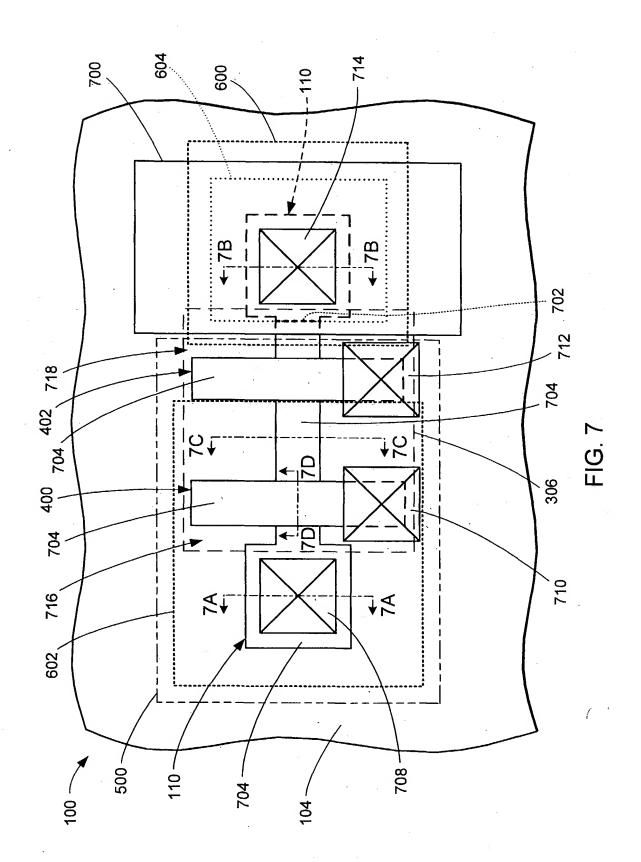
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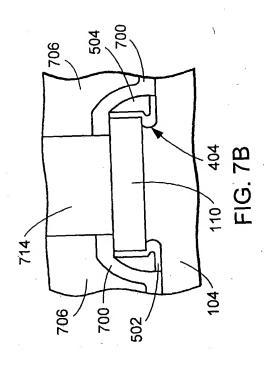


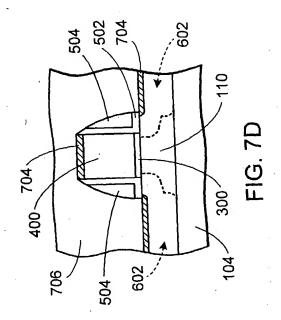
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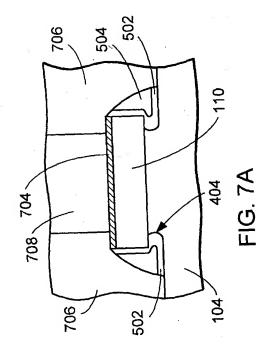
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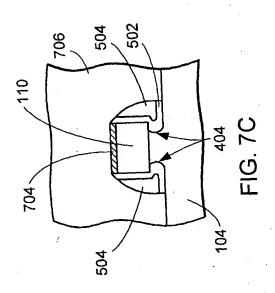


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ITHE. INVISIOR-BASED SRAM AND METHOD USING QUASI-PLANAR FINFET PROCESS FOR THE FABRICATION THEREOF Inventors: Elgin Quek, et al. Docket No.: 1016-027 Contact: Mikio Ishimaru (408) 738-0592

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PROVIDING A SEMICONDUCTOR SUBSTRATE 802

FORMING A HORIZONTAL SEMICONDUCTOR FIN ON TOP OF THE SEMICONDUCTOR SUBSTRATE

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FORMING AN ACCESS TRANSISTOR GATE ON TOP OF THE SEMICONDUCTOR SUBSTRATE AND IN CONTACT WITH THE HORIZONTAL SEMICONDUCTOR FIN 806

FORMING A THYRISTOR GATE ON TOP OF THE SEMICONDUCTOR SUBSTRATE AND IN CONTACT WITH THE HORIZONTAL SEMICONDUCTOR FIN 808

FORMING AN ACCESS TRANSISTOR FROM AT LEAST A PORTION OF THE HORIZONTAL SEMICONDUCTOR FIN AND THE ACCESS TRANSISTOR GATE

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FORMING A THYRISTOR FROM AT LEAST A PORTION OF THE HORIZONTAL SEMICONDUCTOR FIN AND THE THYRISTOR GATE, SUCH THAT THE ACCESS TRANSISTOR IS IN CONTACT WITH THE THYRISTOR 812